

$V_{DSS}$	-12V
$R_{DS(on)}(Max.)$	62mΩ
$I_D$	±3.0A
$P_D$	1.0W

### ●Features

- 1) Low on - resistance.
- 2) High Power small mold Package (TSMT3).
- 3) Pb-free lead plating ; RoHS compliant.
- 4) Halogen Free.

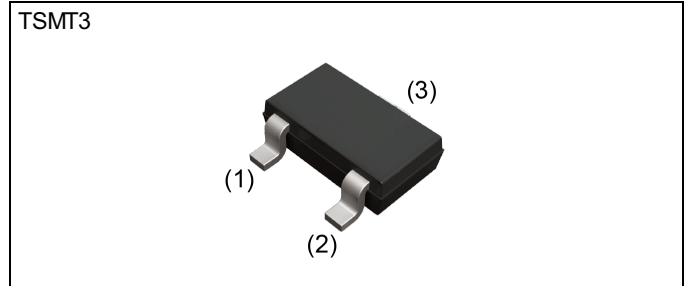
### ●Application

Switching

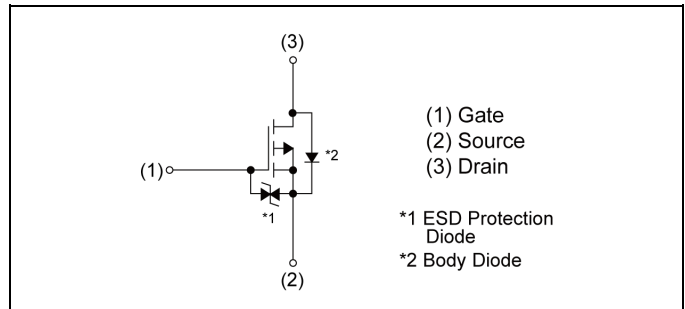
### ●Absolute maximum ratings ( $T_a = 25^{\circ}C$ )

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{DSS}$	-12	V
Continuous drain current	$I_D$	±3.0	A
Pulsed drain current	$I_{D,pulse}^{*1}$	±9.0	A
Gate - Source voltage	$V_{GSS}$	0~-8	V
Power dissipation	$P_D^{*2}$	1.0	W
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55 to +150	°C

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TL
	Marking	SD

## ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}^{*2}$	-	125	-	°C/W

● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-12	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1mA$ referenced to $25^\circ\text{C}$	-	-5.0	-	mV/°C
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -12V, V_{GS} = 0V$	-	-	-10	$\mu\text{A}$
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = -8V, V_{DS} = 0V$	-	-	-10	$\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -6V, I_D = -1mA$	-0.3	-	-1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = -1mA$ referenced to $25^\circ\text{C}$	-	2.7	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*3}$	$V_{GS} = -4.5V, I_D = -3.0A$	-	44	62	m $\Omega$
		$V_{GS} = -2.5V, I_D = -1.5A$	-	55	77	
		$V_{GS} = -1.8V, I_D = -1.5A$	-	75	110	
		$V_{GS} = -1.5V, I_D = -0.6A$	-	90	180	
Transconductance	$g_{fs}^{*3}$	$V_{DS} = -6V, I_D = -3.0A$	3.5	-	-	S

\*1  $P_w \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*2 Mounted on a ceramic board

\*3 Pulsed

**●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	2000	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = -6V$	-	130	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	120	-	
Turn - on delay time	$t_{d(on)}^{*3}$	$V_{DD} \approx -6V, V_{GS} = -4.5V$	-	11	-	ns
Rise time	$t_r^{*3}$	$I_D = -1.5A$	-	40	-	
Turn - off delay time	$t_{d(off)}^{*3}$	$R_L = 4\Omega$	-	160	-	
Fall time	$t_f^{*3}$	$R_G = 10\Omega$	-	60	-	

**●Gate charge characteristics ( $T_a = 25^\circ\text{C}$ )**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{*3}$	$V_{DD} \approx -6V, I_D = -3A$ $V_{GS} = -4.5V$	-	16	-	nC
Gate - Source charge	$Q_{gs}^{*3}$		-	2.4	-	
Gate - Drain charge	$Q_{gd}^{*3}$		-	2.2	-	

**●Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	$I_S$	$T_a = 25^\circ\text{C}$	-	-	-0.8	A
Body diode pulse current	$I_{SP}^{*1}$		-	-	-9.0	
Forward voltage	$V_{SD}^{*3}$	$V_{GS} = 0V, I_S = -3.0A$	-	-	-1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve



Fig.2 Maximum Safe Operating Area

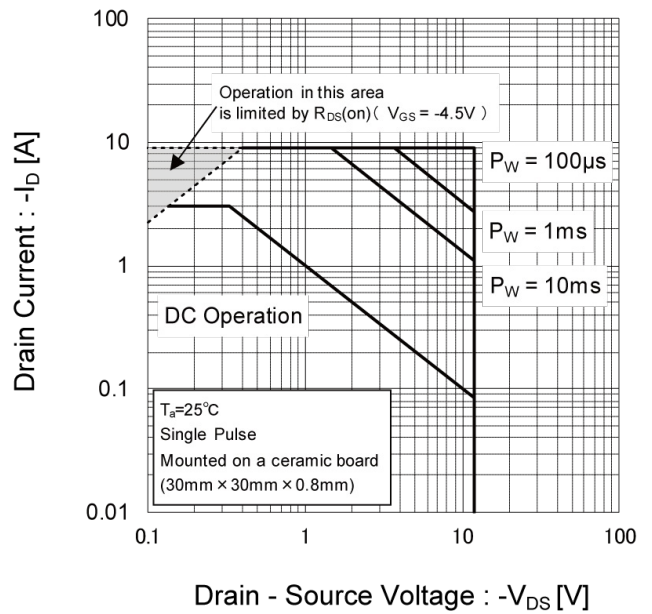


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

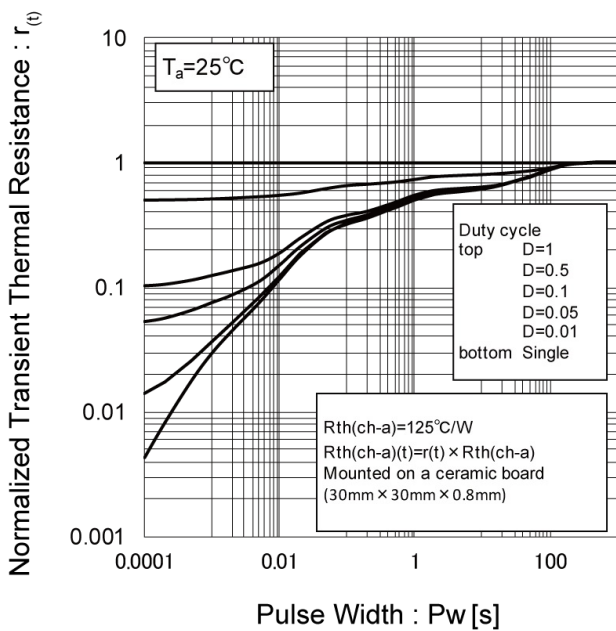
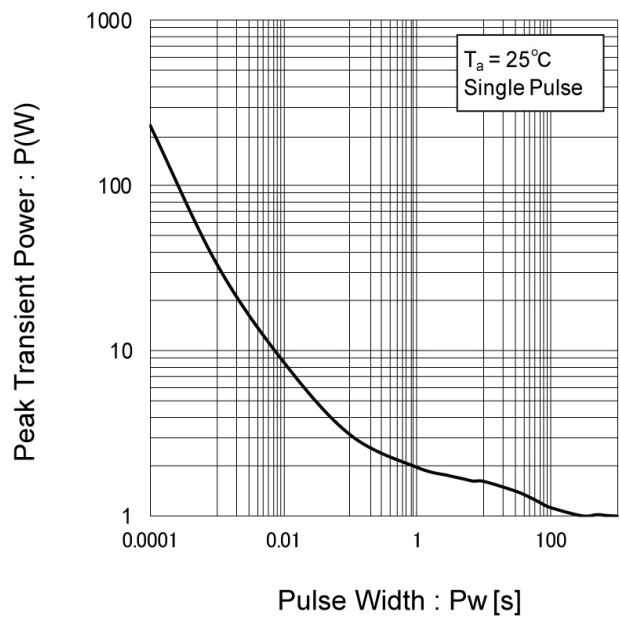


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

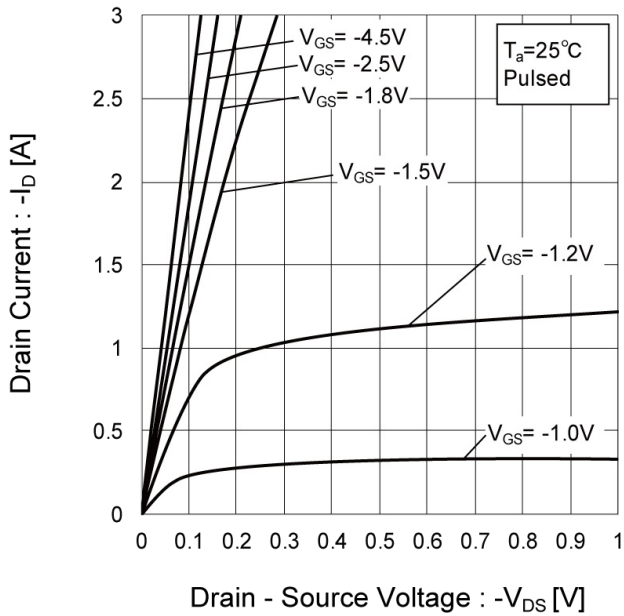


Fig.6 Typical Output Characteristics(II)

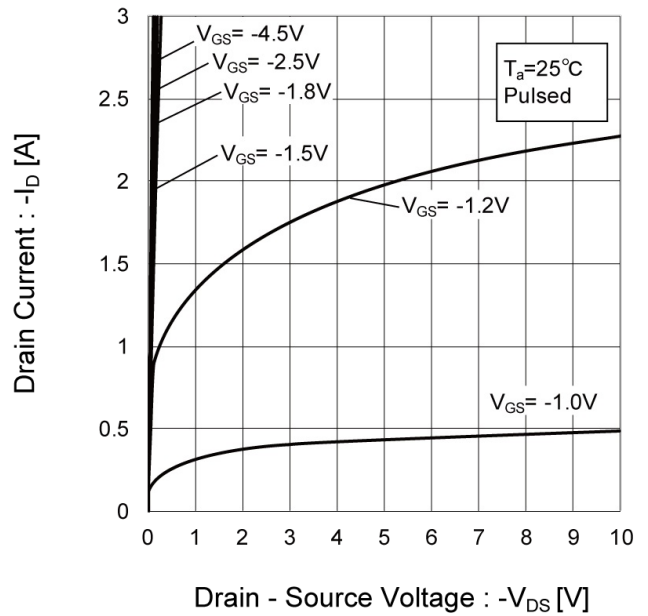


Fig.7 Breakdown Voltage vs. Junction Temperature

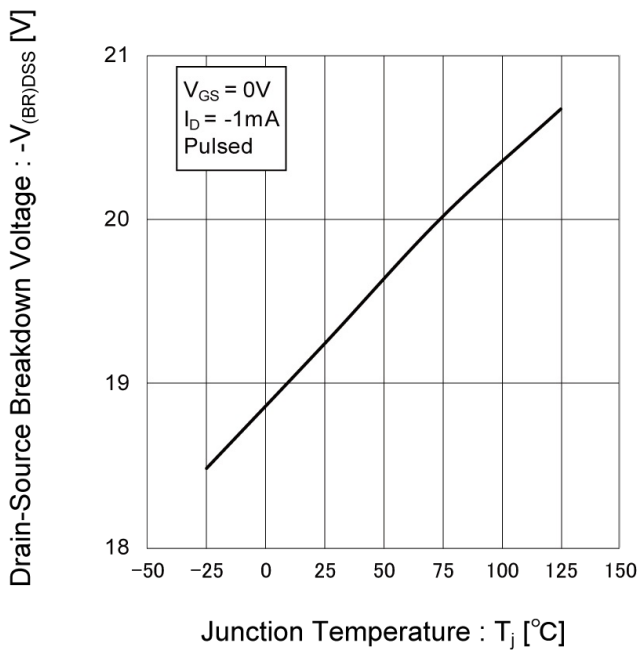
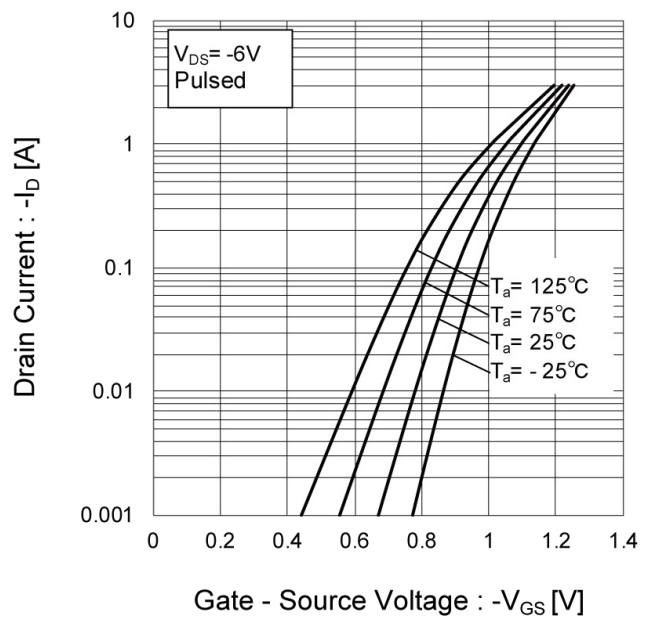


Fig.8 Typical Transfer Characteristics



●Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

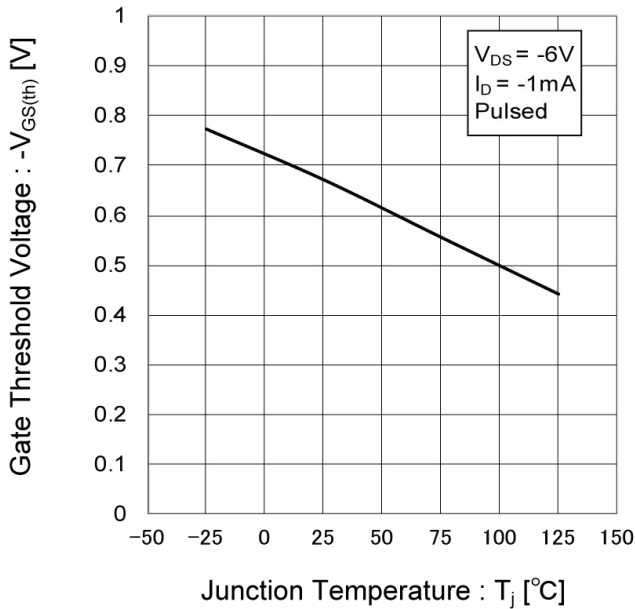


Fig.10 Transconductance vs. Drain Current

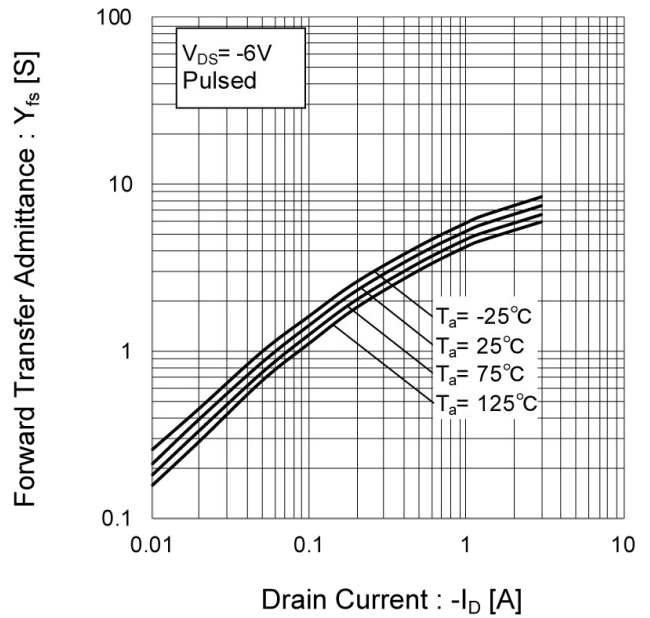


Fig.11 Drain Current Derating Curve

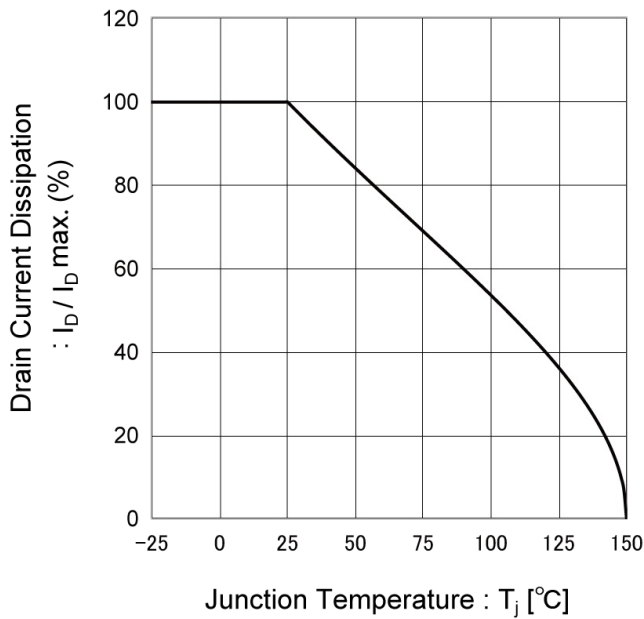
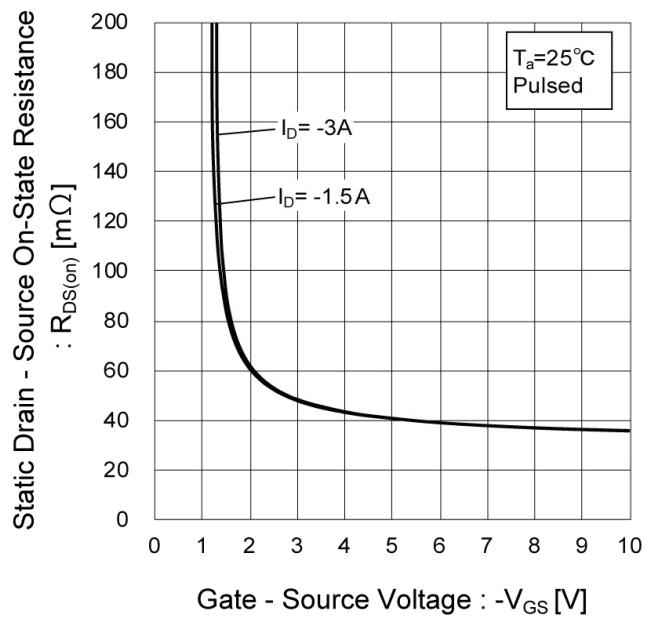


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



● Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

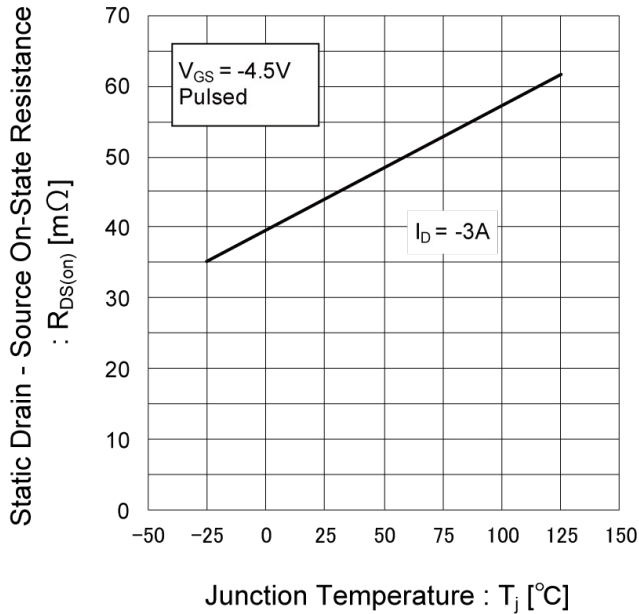


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

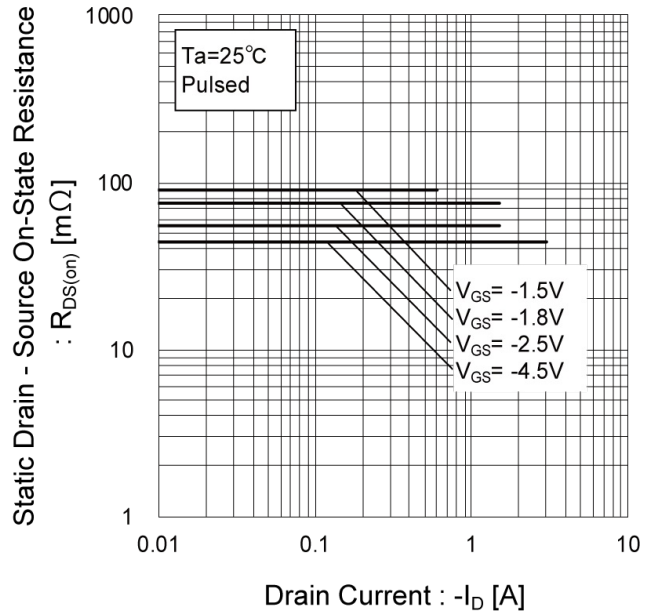


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

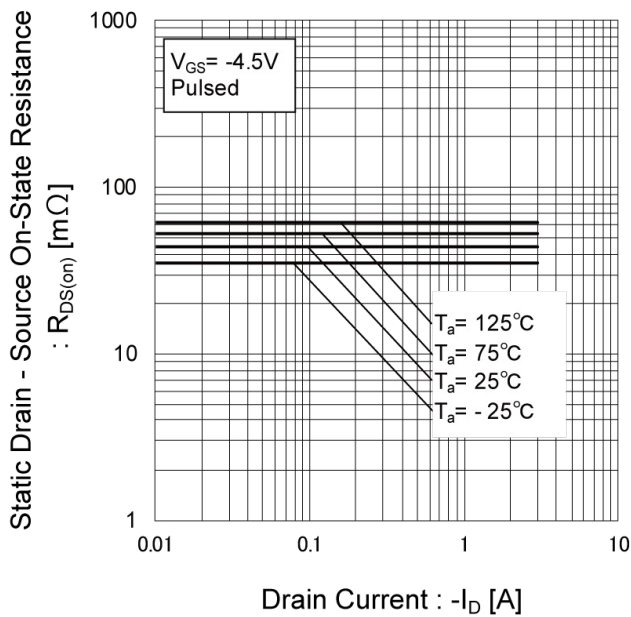
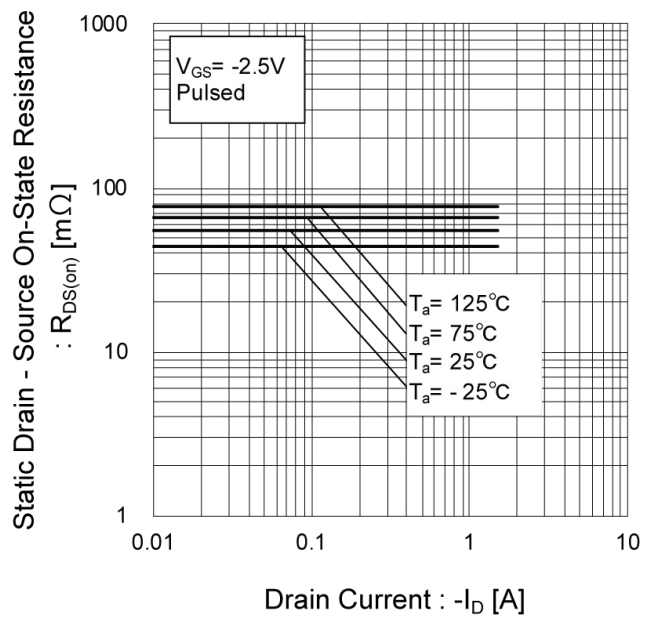


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



● Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

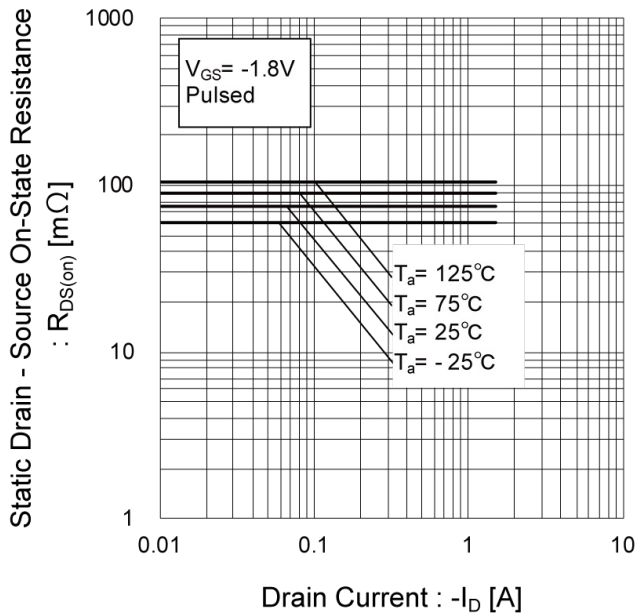


Fig.18 Static Drain - Source On - State Resistance vs. Drain Current(V)

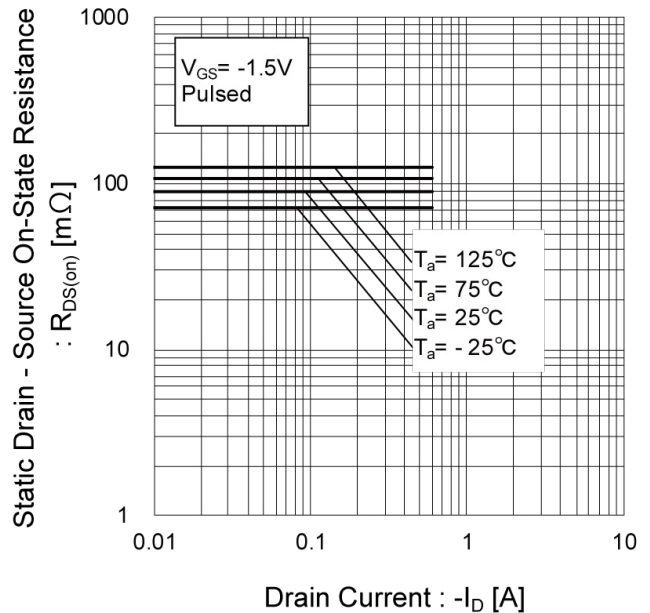


Fig.19 Typical Capacitance vs. Drain - Source Voltage

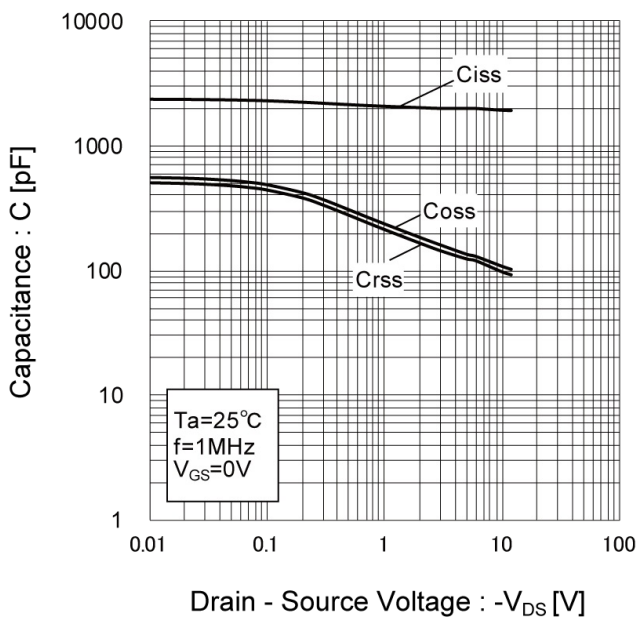
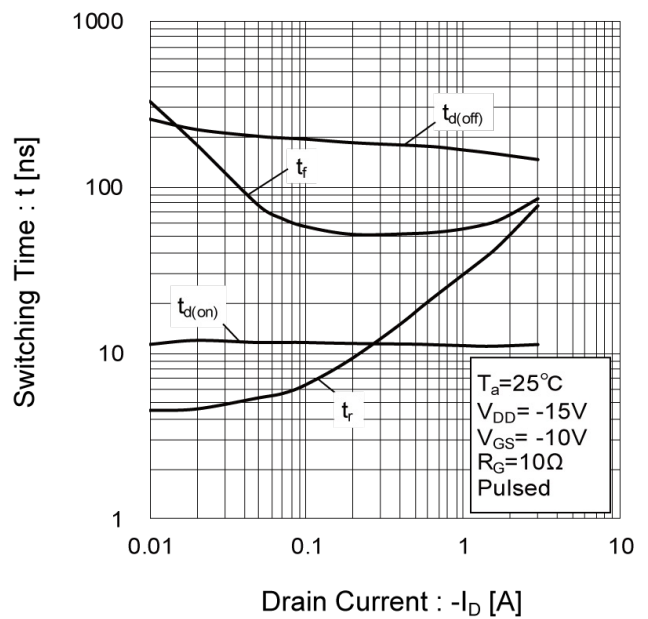


Fig.20 Switching Characteristics





● Electrical characteristic curves

Fig.21 Dynamic Input Characteristics

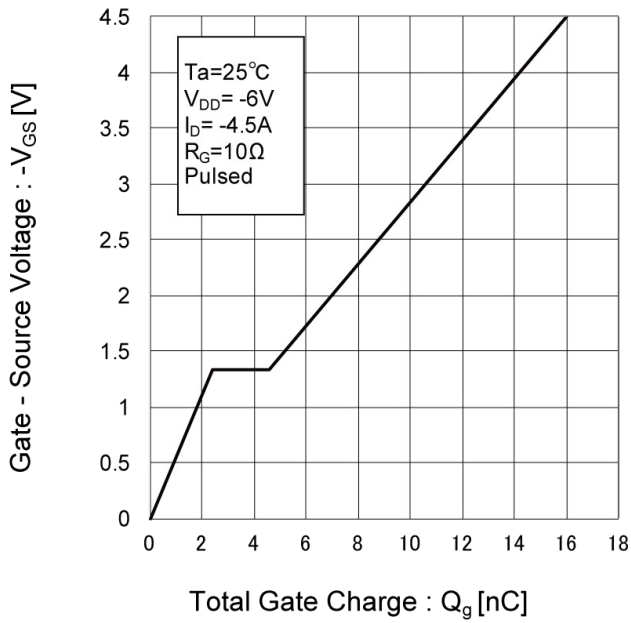
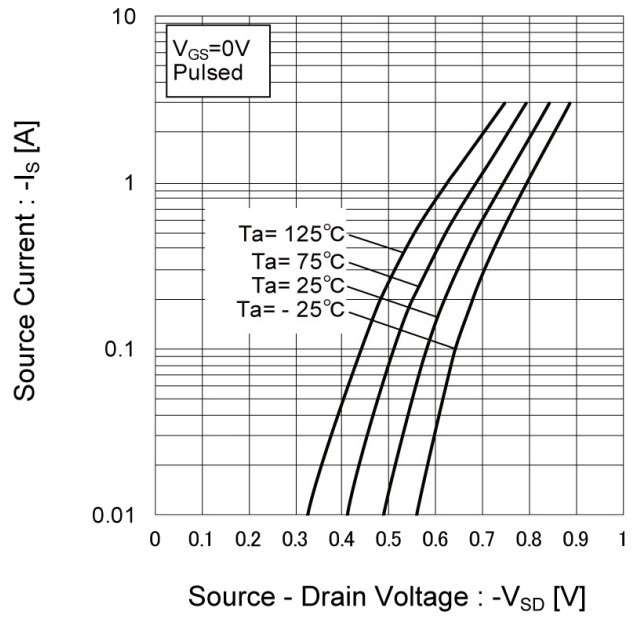


Fig.22 Source Current vs. Source Drain Voltage



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

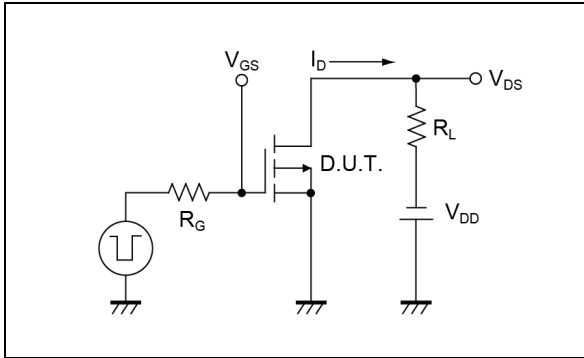


Fig.1-2 Switching Waveforms

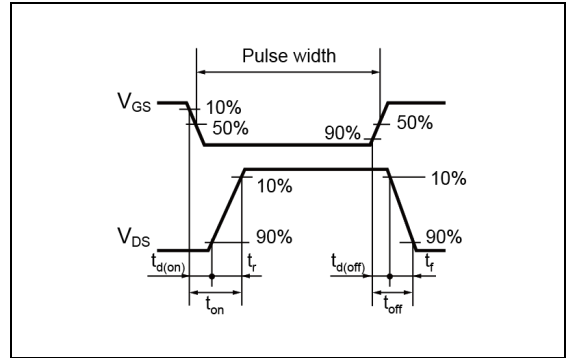


Fig.2-1 Gate Charge Measurement Circuit

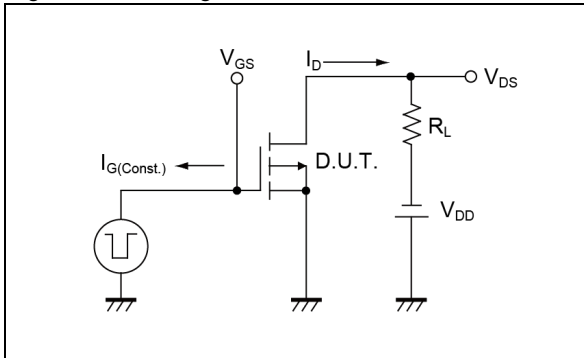
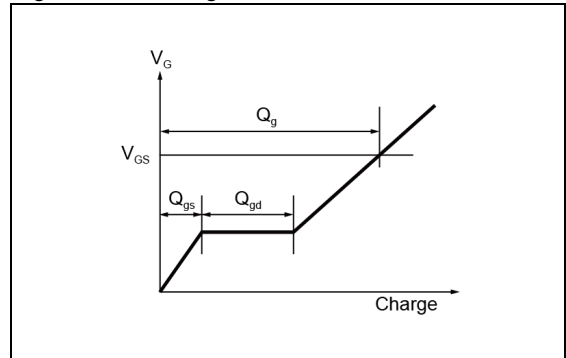
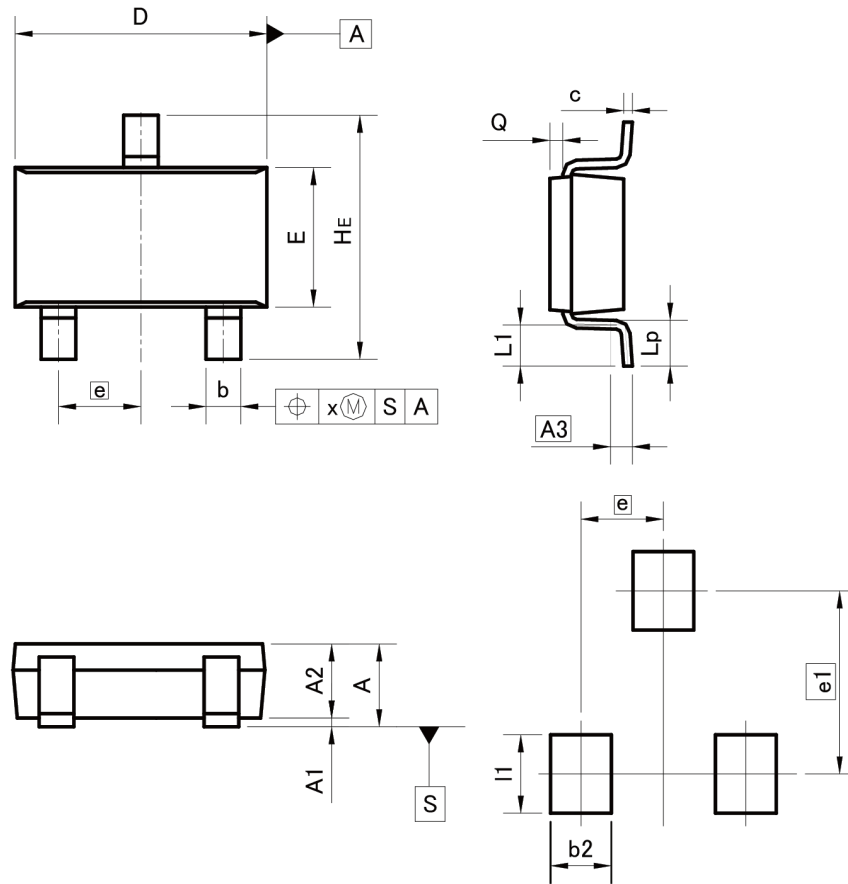


Fig.2-2 Gate Charge Waveform



●Dimensions

TSMT3



Pattern of terminal position areas  
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.00	-	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	-	0.20	-	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.70	-	0.028
e1	2.10		0.083	
l1	-	0.90	-	0.035

Dimension in mm/inches

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